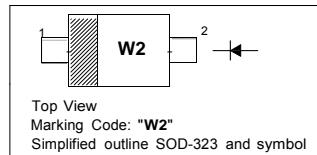


Silicon Epitaxial Planar Switching Diode

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---|-------------|---------------|------------------|
| Peak Reverse Voltage | V_{RM} | 40 | V |
| Reverse Voltage | V_R | 40 | V |
| Average Forward Current | $I_{F(AV)}$ | 200 | mA |
| Peak Forward Current | I_{FM} | 600 | mA |
| Non-Repetitive Peak Forward Surge Current ($t = 1 \text{ s}$) | I_{FSM} | 1 | A |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|---|----------|-----------|------|
| Forward Voltage at $I_F = 200 \text{ mA}$ | V_F | 1.1 | V |
| Reverse Current at $V_R = 15 \text{ V}$ at $V_R = 35 \text{ V}$ | I_R | 50 500 | nA |
| Total Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$ | C_T | 4 | pF |
| Reverse Recovery Time at $V_R = 6 \text{ V}$, $I_F = 10 \text{ mA}$, $I_{rr} = 0.1 \cdot I_R$, $R_L = 100 \Omega$ | t_{rr} | 10 | ns |

1ST112WS
